

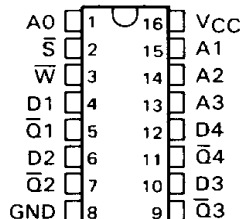
SN54S189B, SN54S289B, SN74S189B, SN74S289B **64-BIT HIGH-PERFORMANCE** **RANDOM-ACCESS MEMORIES**

STATIC RANDOM-ACCESS MEMORIES

- Fully Decoded RAMs Organized as 16 Words of Four Bits Each
- Schottky-Clamped for High Speed:
Read Cycle Time . . . 25 ns Typical
Write Cycle Time . . . 25 ns Typical
- Choice of Three-State or Open-Collector Outputs
- Compatible with Most TTL and I^2L Circuits
- Chip-Select Input Simplifies External Decoding

SN54S189B, SN54S289B . . . J OR W PACKAGE
SN74S189B, SN74S289B . . . J OR N PACKAGE

(TOP VIEW)



description

These 64-bit active-element memories are monolithic Schottky-clamped transistor-transistor logic (TTL) arrays organized as 16 words of four bits each. They are fully decoded and feature a chip-select input to simplify decoding required to achieve expanded system organization. The memories feature p-n-p input transistors that reduce the low-level input current requirement to a maximum of -0.25 milliamperes, only one-eighth that of a Series 54S/74S standard load factor. The chip-select circuitry is implemented with minimal delay times to compensate for added system decoding.

write cycle

The information applied at the data input is written into the selected location when the chip-select input and the write-enable input are low. While the write-enable input is low, the 'S189B output is in the high-impedance state and the 'S289B output is off. When a number of outputs are bus-connected, this high-impedance or off state will neither load nor drive the bus line, but it will allow the bus line to be driven by another active output or a passive pull-up.

read cycle

The stored information (complement of information applied at the data input during the write cycle) is available at the output when the write-enable input is high and the chip-select input is low. When the chip-select input is high, the 'S189B output will be in the high-impedance state and the 'S289B output will be off.

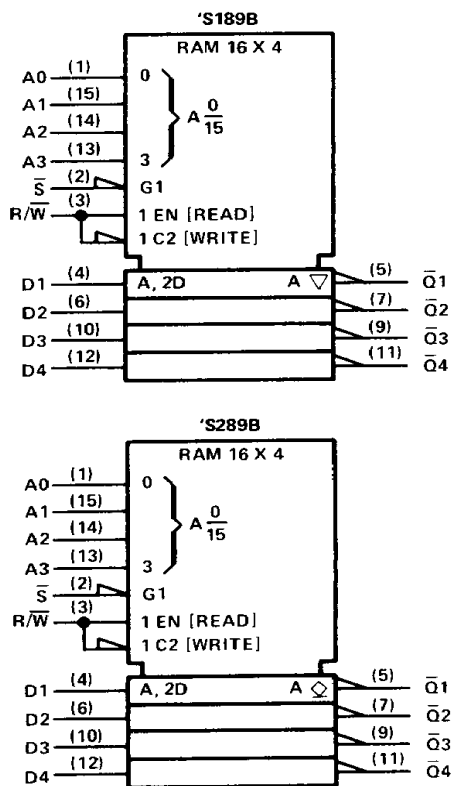
FUNCTION TABLE

FUNCTION	INPUTS		'S189B OUTPUT	'S289B OUTPUT
	CHIP SELECT	WRITE ENABLE		
Write	L	L	High Impedance	Off
Read	L	H	Complement of Data Entered	Complement of Data Entered
Inhibit	H	X	High Impedance	Off

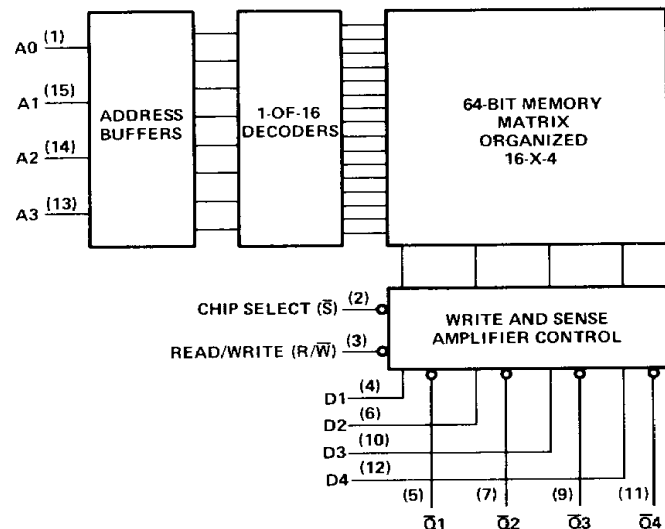
H = high level, L = low level, X = irrelevant

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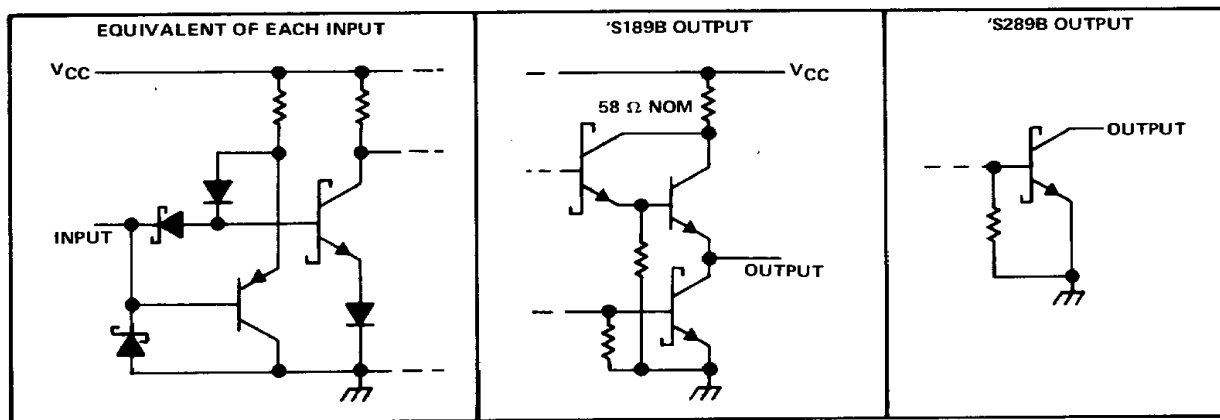
logic symbols



functional block diagram



schematics of inputs and outputs



SN54S189B, SN54S289B, SN74S189B, SN74S289B
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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (see Note 1)	7 V
Input voltage	5.5 V
Off-State output voltage	5.5 V
Operating free-air temperature range: SN54S' Circuits	–55 °C to 125 °C
SN74S' Circuits	0 °C to 70 °C
Storage temperature range	–65 °C to 150 °C

NOTE 1: Voltage values are with respect to network ground terminal.

recommended operating conditions

		SN54S'			SN74S'			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC}		4.5	5	5.5	4.75	5	5.25	V
High-level output voltage, V_{OH}	'S289B			5.5			5.5	V
High-level output current, I_{OH}	'S189B			–2			–6.5	mA
Low-level output current, I_{OL}				16			16	mA
Width of write pulse (write enable low), $t_{W(wr)}$		25			25			ns
Setup time	Address before write pulse, $t_{su(da)}$	0↓			0↓			ns
	Data before end of write pulse, $t_{su(da)}$	25↑			25↑			
	Chip-select before end of write pulse, $t_{su(S)}$	25↑			25↑			
Hold time	Address after write pulse, $t_{h(ad)}$	3↑			0↑			ns
	Data after write pulse, $t_{h(da)}$	0↑			0↑			
	Chip-select after write pulse, $t_{h(S)}$	0↑			0↑			
Operating free-air temperature, T_A		–55		125	0		70	°C

↑ ↓ The arrow indicates the transition of the write-enable input used for reference: ↑ for the low-to-high transition, ↓ for the high-to-low transition.

SN54S189B, SN54S289B, SN74S189B, SN74S289B
64-BIT HIGH-PERFORMANCE
RANDOM-ACCESS MEMORIES

electrical characteristics over recommended operating free-air temperature range
(unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	'S189B			'S289B			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IH} High-level input voltage		2			2			V
V _{IL} Low-level input voltage				0.8			0.8	V
V _{IK} Input clamp voltage	V _{CC} = MIN, I _I = -18 mA			-1.2			-1.2	V
V _{OH} High-level output voltage	V _{CC} = MIN, V _{IH} = 2 V, SN54S' V _{IL} = 0.8 V, I _{OH} = MAX SN74S'	2.4	3.4					V
I _{OH} High-level output current	V _{CC} = MIN, V _{IH} = 2 V, V _O = 2.4 V V _{IL} = 0.8 V V _O = 5.5 V						40 100	μA
V _{OL} Low-level output voltage	V _{CC} = MIN, V _{IH} = 2 V, V _{IL} = 0.8 V, I _{OL} = 16 mA	0.35	0.5		0.35	0.5		V
I _{OZH} Off-state output current, high-level voltage applied	V _{CC} = MAX, V _{IH} = 2 V, V _{IL} = 0.8 V, V _{OH} = 2.4 V			50				μA
I _{OZL} Off-state output current, low-level voltage applied	V _{CC} = MAX, V _{IH} = 2 V, V _{IL} = 0.8 V, V _{OL} = 0.4 V			-50				μA
I _I Input current at maximum input voltage	V _{CC} = MAX, V _I = 5.5 V			1			1	mA
I _{IH} High-level input current	V _{CC} = MAX, V _I = 2.7 V			25			25	μA
I _{IL} Low-level input current	V _{CC} = MAX, V _I = 0.5 V			-250			-250	μA
I _{OS} Short-circuit output current [§]	V _{CC} = MAX	-30		-100				mA
I _{CC} Supply current	V _{CC} = MAX, See Note 2	75	110		75	105		mA

NOTE 2: I_{CC} is measured with the read/write and chip-select inputs grounded. All other inputs at 4.5 V, and the outputs open.

'S189B switching characteristics over recommended operating ranges of T_A and V_{CC}
(unless otherwise noted)

PARAMETER	TEST CONDITIONS	SN54S189B			SN74S189B			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
t _{a(ad)} Access time from address	C _L = 30 pF, See Note 3	25		50	25		35	ns
t _{a(S)} Access time from chip select (enable time)		18		25	18		22	ns
t _{SR} Sense recovery time		22		40	22		35	ns
t _{PXZ} Disable time from high or low level	From \bar{S}	12		25	12		17	ns
	From \bar{W}	12		30	12		25	

'S289B switching characteristics over recommended operating ranges of T_A and V_{CC}
(unless otherwise noted)

PARAMETER	TEST CONDITIONS	SN54S289B			SN74S289B			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
t _{a(ad)} Access time from address	C _L = 30 pF, R _{L1} = 300 Ω, R _{L2} = 600 Ω, See Note 3	25		50	25		35	ns
t _{a(S)} Access time from chip-select (enable time)		18		25	18		22	ns
t _{SR} Sense recovery time		22		40	22		35	ns
t _{PLH} Propagation delay time, low-to-high-level output (disable time)	From \bar{S}	12		25	12		17	ns
	From \bar{W}	12		30	12		25	

[†]For conditions shown as MIN or MAX use the appropriate value specified under recommended operating conditions.

[‡]All typical values are at V_{CC} = 5 V, T_A = 25°.

[§]Duration of the short circuit should not exceed one second.

NOTE 3: Load circuits and voltage waveforms are shown in Section 1.